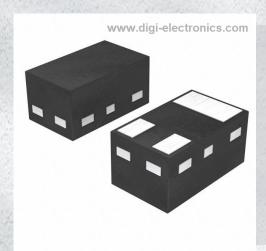


# PDTC115TMB,315 Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number PDTC115TMB,315-DG

> Manufacturer Nexperia USA Inc.

Manufacturer Product Number PDTC115TMB,315

> Description TRANS PREBIAS NPN 50V 0.1A 3DFN

Pre-Biased Bipolar Transistor (BJT) NPN - Pre-Biase **Detailed Description** 

d 50 V 100 mA 230 MHz 250 mW Surface Mount DFN



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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PDTC115TMB,315	Nexperia USA Inc.
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	100 kOhms
DC Current Gain (hFE) (Min) @ Ic, Vce:	Vce Saturation (Max) @ lb, lc:
100 @ 1mA, 5V	150mV @ 250μA, 5mA
Current - Collector Cutoff (Max):	Frequency - Transition:
1μΑ	230 MHz
Power - Max:	Grade:
250 mW	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
3-XFDFN	DFN1006B-3
Base Product Number:	
PDTC115	

## **Environmental & Export classification**

8541.21.0075

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



NPN resistor-equipped transistor; R1 = 100 kΩ, R2 = open Rev. 1 — 21 June 2012 Product data s

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA115TMB.

#### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

#### 1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Replaces general-purpose transistors in digital applications
- Mobile applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	M	in	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-		-	50	V
Io	output current		-		-	100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	70	)	100	130	kΩ



NPN resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = open

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)	1	3
3	0	output (collector)	2 Transparent top view	1 R1
			DFN1006B-3 (SOT883B)	sym012

## 3. Ordering information

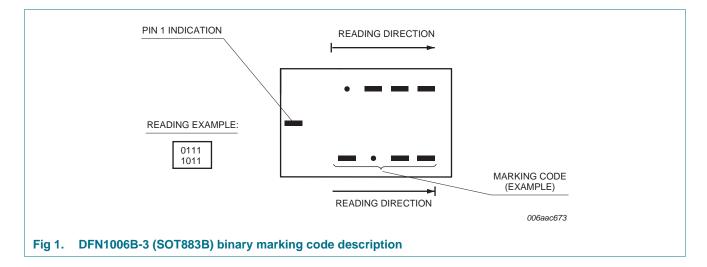
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTC115TMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

### 4. Marking

Table 4. Marking codes

Type number	Marking code
PDTC115TMB	0011 0010



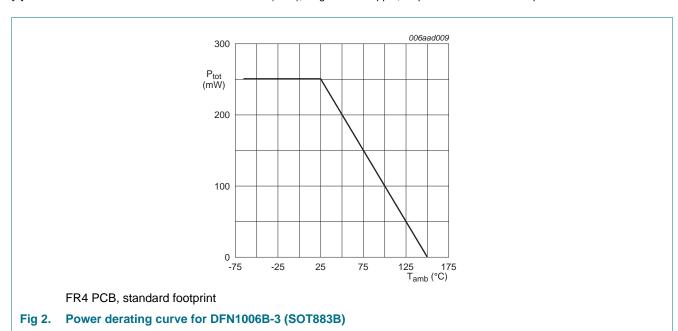
## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	5	V
Io	output current			-	100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

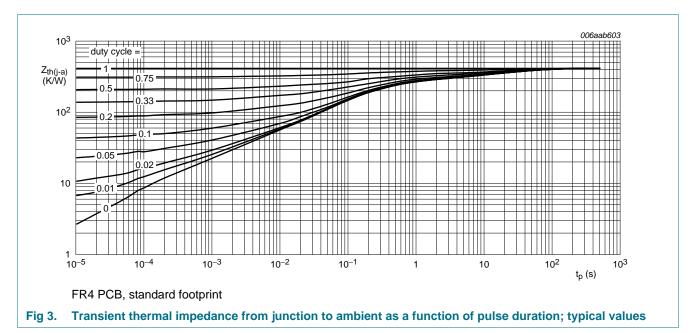


#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



#### 7. Characteristics

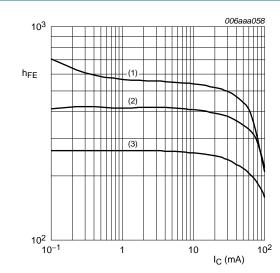
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	1	μA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; $I_{C}$ = 1 mA; $T_{amb}$ = 25 °C		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C		70	100	130	kΩ
C <sub>C</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[1]	-	230	-	MHz

[1] Characteristics of built-in transistor.

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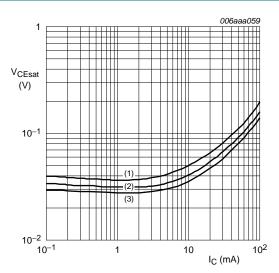
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 4. DC current gain as a function of collector current; typical values



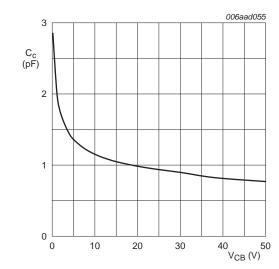
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

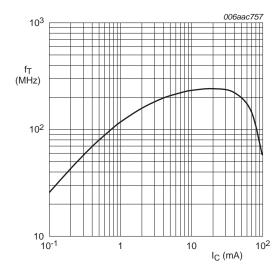
(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz; T<sub>amb</sub> = 25 °C

Fig 6. Collector capacitance as a function of collector-base voltage; typical values of built-in transistor



 $V_{CE} = 5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

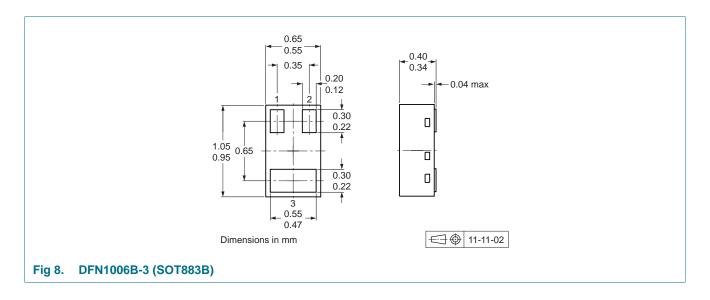
Fig 7. Transition frequency as a function of collector current; typical values of built-in transistor

### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

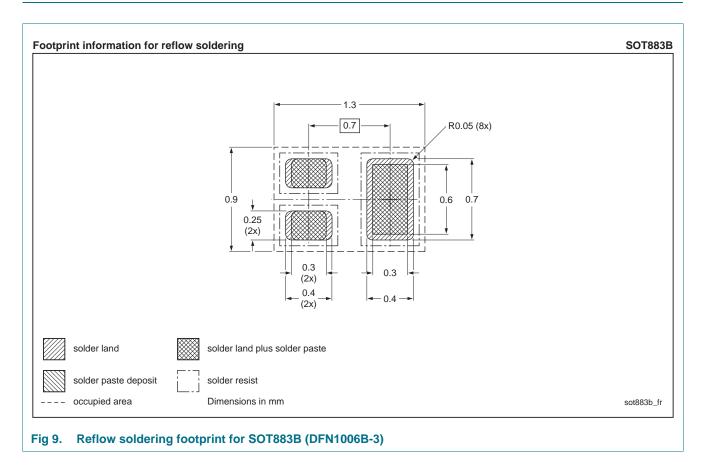
### 9. Package outline



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NPN resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = open

## 10. Soldering



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NPN resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = open

## 11. Revision history

#### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC115TMB v.1	20120621	Product data sheet	-	-

NPN resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = open

#### 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions'
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PDTC115TMB

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## PDTC115TMB

#### NPN resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = open

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## PDTC115TMB

NPN resistor-equipped transistor; R1 = 100 k $\Omega$ , R2 = open

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